

3V, 5GHz LINEAR POWER AMPLIFIER

RoHS Compliant & Pb-Free Product

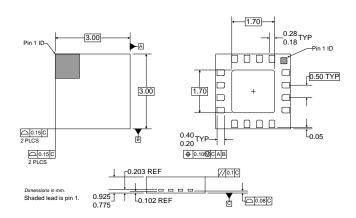
Typical Applications

- IEEE802.11a/n WLAN Applications
- HyperLAN
- Wireless LAN Systems

- Commercial and Consumer Systems
- Portable Battery-Powered Equipment
- Spread-Spectrum and MMDS Systems

Product Description

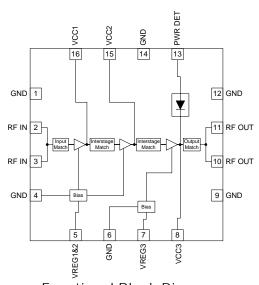
The RF5300 is a linear, medium-power, high-efficiency amplifier IC designed specifically for battery-powered WLAN applications such as PC cards, mini PCI, and compact flash applications. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 5GHz WLAN and other spread-spectrum transmitters. The device is provided in a 16-pin leadless chip carrier with a backside ground. The RF5300 is designed to maintain linearity over a wide range of supply voltage and power output. The RF5300 is designed to reduce end-product BOM count by integrating all matching circuitry onto the chip.



Optimum Technology Matching® Applied

- ☐ Si BJT
 ☐ Si Bi-CMOS
- ✓ GaAs HBT☐ SiGe HBT
- ☐ GaAs MESFET ☐ Si CMOS

- ☐ InGaP/HBT
- ☐ GaN HEMT
- ☐ SiGe Bi-CMOS



Functional Block Diagram

Package Style: QFN, 16-Pin, 3x3

Features

- Single Power Supply 3.0V to 5.0V
- 50Ω Input/Output Impedance
- 30dB Gain (typ. UNII-1 and 2)
- High Linearity
- 4900MHz to 5850MHz Frequency Range

Ordering Information

RF5300 3V, 5GHz Linear Power Amplifier RF5300PCBA-41X Fully Assembled Evaluation Board

RF Micro Devices, Inc. 7628 Thorndike Road Greensboro, NC 27409, USA Tel (336) 664 1233 Fax (336) 664 0454 http://www.rfmd.com

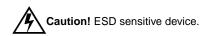
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RF5300

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +6.0	V_{DC}
Power Control Voltage (V _{REG})	-0.5 to 3.5	V
DC Supply Current	600	mA
Input RF Power	+10	dBm
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C
Moisture sensitivity	JEDEC Level 3	

Refer to "Handling of PSOP and PSSOP Products" on page 16-15 for special handling information.



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Doromotor	Specification		l lm!4	Condition		
Parameter	Min.	Тур.	Max. Unit		Condition	
Overall					T=25°C, V _{CC} =3.3V, V _{REG} =2.8V,	
					Freq=4900MHz to 5850MHz	
Frequency Range		4900 to 5850		MHz		
Output Power					With 802.11a modulation (54Mbit/s) meeting	
V 0.0V	40			-ID	spectral mask and EVM requirements	
V _{CC} =3.3V	16			dBm	F=4900MHz to 5000MHz, F=5700MHz to 5850MHz	
	18			dBm	F=5150MHz to 5350MHz	
EVM	10	2.7		иВIII %	1 = 3130 WII 12 to 3330 WII 12	
V _{CC} =3.3V	18	2.1		dBm	F=4900MHz to 5850MHz	
EVM	.0		4	%	1 = 10001/11 12 to 00001/11 12	
V _{CC} =5.0V	19	20	4	dBm	F=4900MHz to 5850MHz	
EVM	10	20	4	%	1 = 4000 Wil 12 to 0000 Wil 12	
Gain (RFP _{OUT} =+15dBm)	26	28	7	dB	F=4900MHz to 5000MHz	
Gain (14.1 1 001 = 1 10 abin)	29	30		dB	F=5150MHz to 5350MHz	
	29	26		dB	F=5700MHz to 5850MHz	
Power Detect (P_detect) Voltage	0.50	0.65	0.70	V _{DC}	RF P _{OUT} =+11dBm (4900MHz to 5850MHz)	
Tower Detect (T_detect) Voltage	1.1	1.3	1.5			
		_	_	V _{DC}	RF P _{OUT} =+18dBm (4900MHz to 5850MHz)	
	1.3	1.5	1.7	V _{DC}	RF P _{OUT} =+19dBm (4900MHz to 5850MHz)	
Power Supply						
Operating Voltage		3.0 to 5.0		V		
Current Consumption		265		mA	P_{OUT} =18dBm, V_{CC} =3.3V, V_{REG} =+2.8V	
		195		mA	Idle current, V _{CC} =3.3V, V _{REG} =2.8V	
V _{REG} Current (Total)		5	10	mA	$V_{CC}=3.3V$	
		10	15	mA	V _{CC} =5.0V	

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Pin	Function	Description	Interface Schematic
1	GND	Ground.	
2	RF IN	RF input. Input is matched to 50Ω and DC block is provided internally.	VCC1 INTERSTAGE MATCH MATCH
3	RFIN	Same as pin 2.	See pin 2.
4	GND	Ground.	
5	VREG1&2	First and second stage input bias. This pin requires a regulated supply to maintain nominal bias current.	VREG1 O-BIAS VREG2 O-BIAS BIAS GND1 GND2
6	VREG3/ GND	Ground for third stage bias circuit. Attach to RF ground approximately 100mils to ground from package.	See pin 5.
7	VREG3	Third stage input bias. This pin requires a regulated supply to maintain a nominal bias current.	
8	VCC3	Third stage supply bias. This pin is sensitive to bypass capacitors which should be placed approximately 100mils from package and resonate 5GHz to ground.	
9	GND	Ground.	
10	RF OUT	RF output. Output is matched to 50Ω and DC block is provided.	VCC2 OUTPUT ORF OUT
11	RF OUT	Same as pin 10.	See pin 10.
12	GND	Ground.	
13	PWR DET	Provides an output voltage proportional to the RF level.	
14	GND	Ground.	
15	VCC2	Supply voltage for the second stage. Bypass capacitor is needed to provide isolation from VCC1 and VCC3.	
16	VCC1	Supply voltage for the first stage.	
Pkg Base	GND	Ground connection. The backside of the package should be connected to the ground plane through a short path (i.e., vias under the device will be required).	

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RF5300

Theory of Operation

The RF5300 is a three-stage device with a nominal gain of 28dB to 30dB in the 4.9GHz to 5.850GHz ISM band. The RF5300 is designed primarily for IEEE802.11a/n WLAN applications where the available supply voltage and current are limited. This amplifier will operate to (and below) the lowest expected voltage made available by a typical PCMCIA slot in a laptop PC, and will maintain required linearity at decreased supply voltages.

The RF5300 requires only a single positive supply of 3.0V nominal (or greater) to operate to full specifications. Power control is provided through two bias control input pins (VREG1, VREG2, and VREG3), but in most applications these are tied together and used as a single control input.

There is no external matching required on the input and output of the part, thus allowing minimal bill of material (BOM) parts count in end applications. Both the input and the output of the device are DC-blocked.

For best results, the PA circuit layout from the evaluation board should be copied as closely as possible, particularly the ground layout and ground vias. Other configurations may also work, but the design process is much easier and quicker if the layout is copied from the RF5300 evaluation board. Gerber files of our designs are available on request.

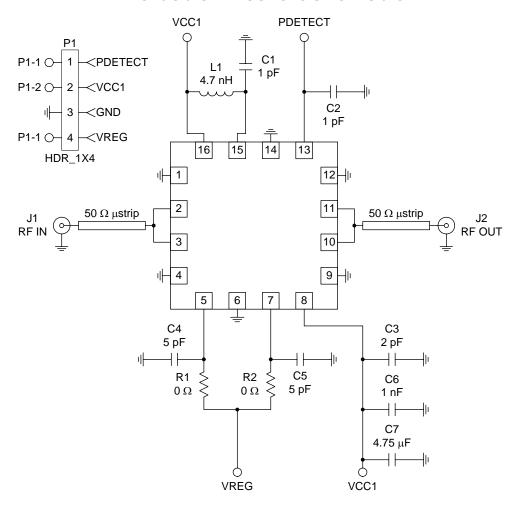
The RF5300 is not a difficult part to implement, but care in circuit layout and component selection is always advisable when designing circuits to operate at 5GHz.

It is important to isolate VCC1 from other RF and low-frequency bypass capacitors on this supply line. This can be accomplished using a suitably-long transmission line which is RF shorted on the other end as described above. Ideally the length of this line will be a quarter wavelength, but it only needs to be long enough so that the effects of other supply bypass capacitors on the VCC1 line are minimized. If board space is a concern, this isolation can also be accomplished with an RF choke inductor or ferrite bead.

The RF5300 has primarily been characterized with a voltage on VREG1, VREG2, and VREG3 of $2.8V_{DC}$. However, the RF5300 will operate from a wide range of control voltages. If you prefer to use a control voltage that is significantly different than $2.8V_{DC}$, contact RFMD Sales or Applications Engineering for additional data and guidance.

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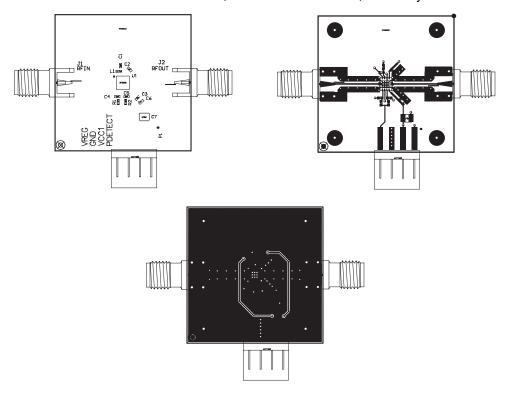
Evaluation Board Schematic



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Evaluation Board Layout Board Size 1.2" x 1.2"

Board Thickness 0.032", Board Material FR-4, Multi-Layer



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